

PERSISTENT MEMORY – WHICH MODE DO I WANT? WHERE ARE THE "GOTCHAS" HIDDEN?

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AGENDA

- Intro & Context
- Part 1: Architectural Background
- Part 2: Performance Characteristics
- Part 3: Monitoring & Tuning
- Summary & Resources



FOCUS OF THIS PRESENTATION



General Workload Optimization Process (Iterative):

Create Workload Collect & Analyze Data using Intel® VTune™ Platform Profiler, Intel® VTune™ Amplifier XE

Find
Optimization
Opportunities

Tune Workload

We Will Address

What architectural conditions should I be monitoring, and why?

How is my workload utilizing the hardware?

We Won't Address

How do I use PMDK/SPDK?

How do I use the Intel analyzer tools to collect data?

Are there better design patterns I could use For more performance?

How do I change my code?

Could I configure my O/S and environment for better performance?



PART 1: KEY ARCHITECTURAL CONCEPTS: 2ND GENERATION INTEL® XEON® SCALABLE PROCESSORS, OPTANE™ DC PERSISTENT MEMORY





GET READY FOR TERMS, FLOWS, AND DIAGRAMS!



Why?

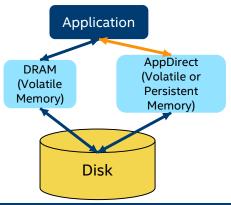
To establish background in the architecture, which will be needed to understand the monitoring and tuning strategies to optimize.



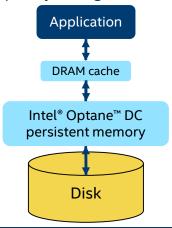
INTEL® OPTANE™ DC PERSISTENT MEMORY MODES



- Application Direct (AppDirect) mode uses Intel®
 Optane™ DC persistent memory to provide
 volatile or non-volatile (persistent) memory to
 applications
 - Intel® Optane™ DC persistent memory modules are accessed by loads and stores or using persistent memory libraries
 - Intel® Optane™ DC persistent memory is treated as a separate region of memory from DRAM



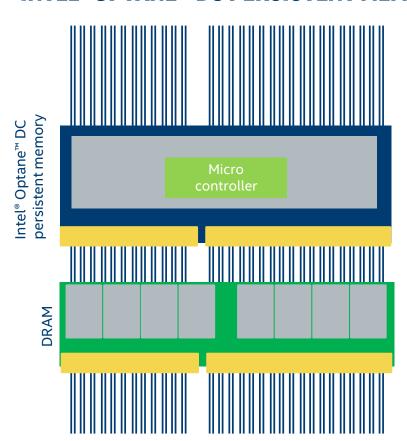
- Memory mode uses Intel® Optane™ DC persistent memory as an additional tier of memory between DRAM and disk
 - DRAM is a direct-mapped cache for Intel® Optane™ DC persistent memory, which is transparent to the application developers
 - Intel® Optane™ DC persistent memory tier acts as temporary storage for disk data (not persistent)





INTEL® OPTANE™ DC PERSISTENT MEMORY MODULE CONCEPTS



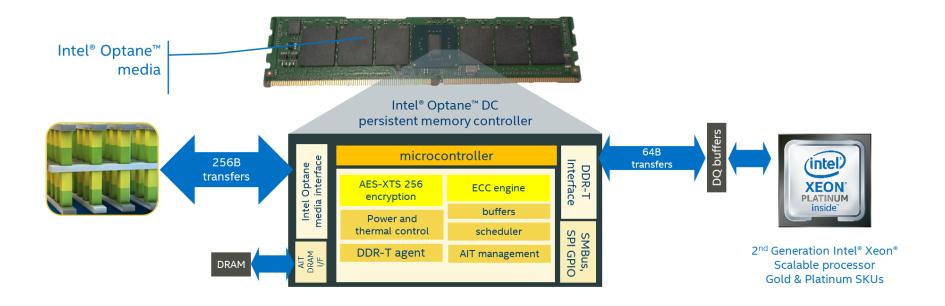


Up to 6 Intel® Optane™ DC persistent memory modules per socket

- 3 modules per memory controller, 2 memory controllers per socket.
- DRAM DIMMS share the same bus with Intel[®] Optane[™] DC persistent memory modules.

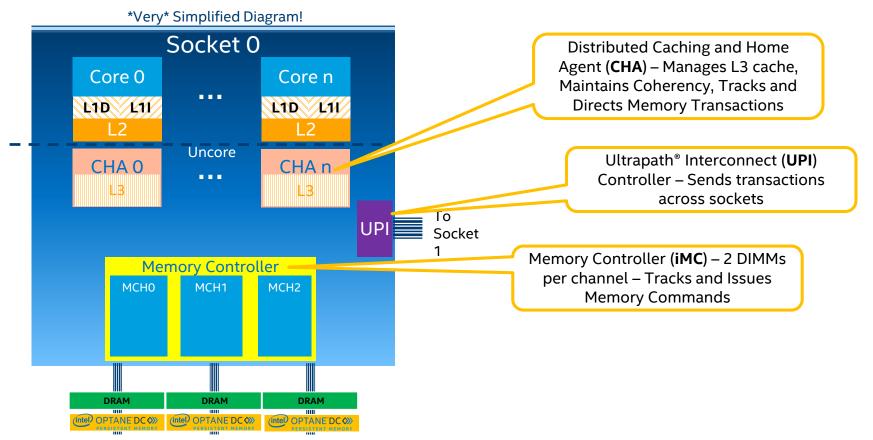
AN IMPORTANT MICROCONTROLLER CONCEPT





FEW KEY COMPONENTS IN THE SYSTEM

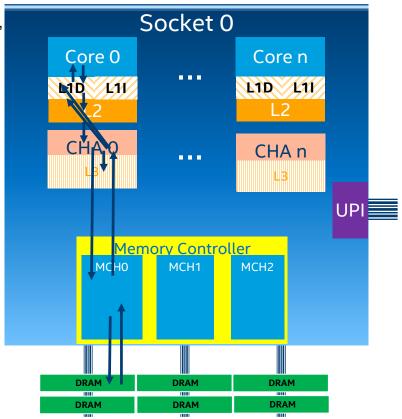




A BASIC MEMORY TRANSACTION TO DRAM



*Simplified! Some steps not shown, Some components not depicted

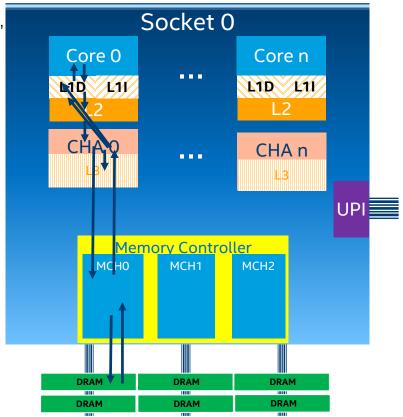




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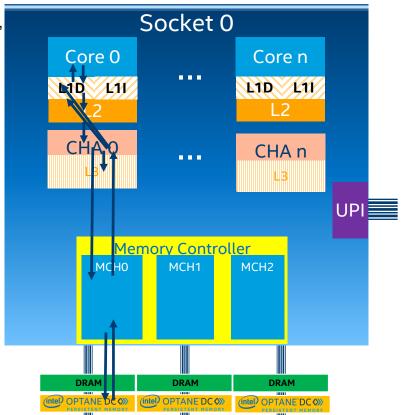




READ TRANSACTION TO APPDIRECT MEMORY



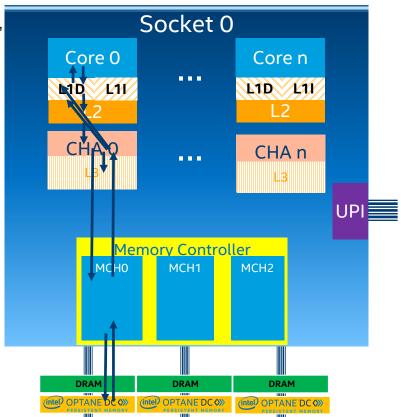
*Simplified! Some steps not shown, Some components not depicted



READ TRANSACTION TO APPDIRECT MEMORY



*Simplified! Some steps not shown, Some components not depicted



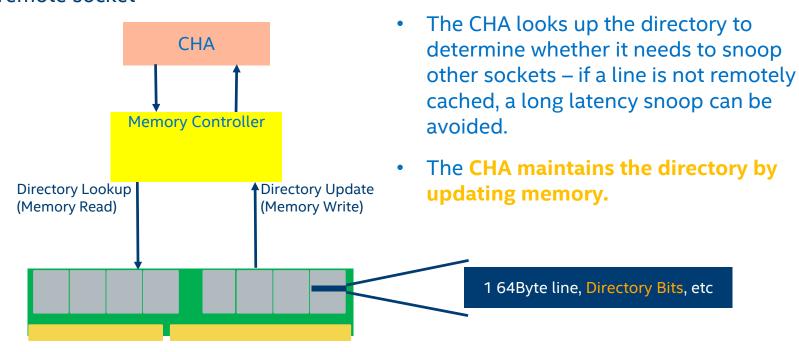


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ONE IMPORTANT CONCEPT: THE DIRECTORY



Directory is structure stored in memory that tracks whether a line is cached in a remote socket





KEY TAKEWAYS OF APPDIRECT MODE

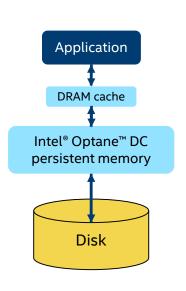
Performance varies by workload

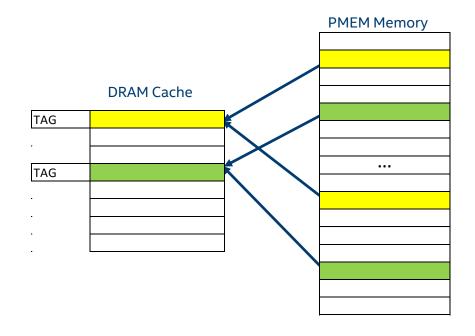
- AppDirect memory can be used for persistence
- Lower latency than disk accesses
- Enable larger memory data structures
 - Move in-memory data structures from disk to AD memory
 - Move hot data structures to DRAM, warm data structures to Intel[®] Optane DC persistent memory
- Optimize for NUMA awareness



HOW IS INTEL® OPTANE™ DC PERSISTENT MEMORY IS CACHED IN DRAM? OPTANE™DC OPTANE™DC OPTANE™DC OPTANE™DC OPTANE™DC







READ TRANSACTION TO MEMORY MODE - DRAM CACHE HIT



Socket 0 *Simplified! Some steps not shown, Some components not depicted Core 0 Core n 111 L_{1D} **L11** L1D CHA n **UPI** Memory Controller M CHO MCH1 MCH2 TAG CHECK: NEAR MEMORY (DRAM CACHE) HIT DRAM **DRAM** (intel) OPTANE DCO



READ TRANSACTION TO MEMORY MODE - DRAM CACHE HIT



Socket 0 *Simplified! Some steps not shown, Some components not depicted Core 0 Core n 111 L_{1D} **L11** L1D CHA n **UPI** Memory Controller M 2H0 MCH1 MCH2 TAG CHECK: NEAR MEMORY (DRAM CACHE) HIT DRAM DRAM



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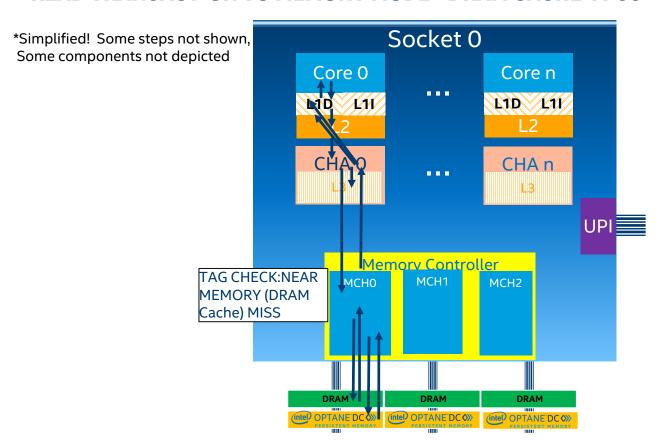
READ TRANSACTION TO MEMORY MODE - DRAM CACHE MISS



Socket 0 *Simplified! Some steps not shown, Some components not depicted Core 0 Core n 111 L_{1D} **L11** L1D CHA n **UPI** Memory Controller TAG CHECK:NEAR MCH1 M CHO MCH2 MEMORY (DRAM Cache) MISS DRAM DRAM

READ TRANSACTION TO MEMORY MODE - DRAM CACHE MISS





KEY TAKEAWAYS OF MEMORY MODE



Good locality means near-DRAM performance

- Cache hit: latency same as DRAM
- Cache miss: latency DRAM + Intel® Optane™ DC persistent memory

Performance varies by workload

- Best workloads have the following traits:
 - Good locality for high DRAM cache hit rate
 - Low memory bandwidth demand
 - #reads > #writes
- Also take into consideration
 - Config vs. Workload size
- Optimize for NUMA awareness





PART 2: PERFORMANCE CHARACTERISTICS OF INTEL® OPTANE™ DC PERSISTENT MEMORY







INTEL® OPTANE™ DC PERSISTENT MEMORY PERFORMANCE DETAILS

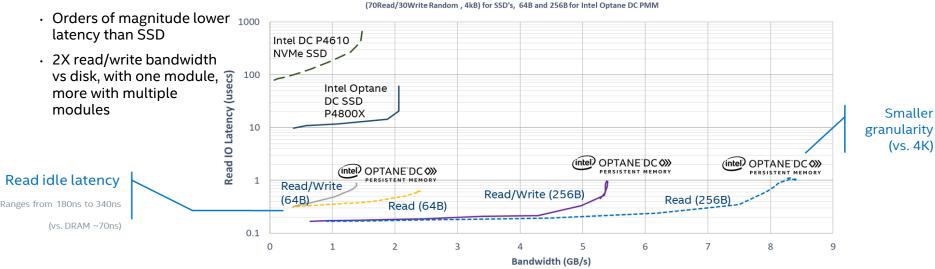
- Intel® Optane™ DC persistent memory is programmable for different power limits for power/performance optimization
 - 12W 18W, in 0.25 watt granularity for example: 12.25W, 14.75W, 18W
 - Higher power settings give best performance
- Performance varies based on traffic pattern
 - Contiguous 4 cacheline (256B) granularity vs. single random cacheline (64B) granularity
 - Read vs. writes

Granularity	Traffic	Module	Bandwidth
256B (4x64B)	Read	256GB, 18W	8.3 GB/s
256B (4x64B)	Write		3.0 GB/s
256B (4x64B)	2 Read/1 Write		5.4 GB/s
64B	Read		2.13 GB/s
64B	Write		0.73 GB/s
64B	2 Read/1 Write		1.35 GB/s



INTEL® OPTANE™ DC PERSISTENT MEMORY LATENCY





1. 256B granularity (64B accesses). Note 4K granularity gives about same performance as 256B

Performance results are based on testing as of Feb 22, 2019 and may not reflect all publicly available security updates. No product can be absolutely secure.

Results have been estimated based on tests conducted on pre-production systems, and provided to you for informational purposes. Software and workloads used in performance tests may have been optimized for performance only on Intel microprocessors. Performance tests, such as SYSmark and MobileMark, are measured using specific computer systems, components, software, operations and functions. Any change to any of those factors may cause the results to vary. You should consult other information and performance tests to assist you in fully evaluating your contemplated purchases, including the performance of that product when combined with other products. For more information go to www.intel.com/benchmarks. Configuration: see slide 36 and 37...





PART 3: MONITORING AND TUNING STRATEGIES





APPDIRECT MODE

OPTIMIZATION OPPORTUNITY: READ/WRITE RATIO

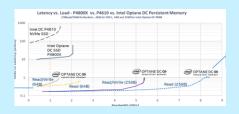


Workload Behavior:

Write-intensive application

Why?

Reads to Intel® Optane Persistent Memory are faster than writes



How to detect this opportunity?

Use Intel® VTune™ Platform Profiler

 Persistent memory traffic: Read/Write throughput

Use Intel® VTune™ Amplifier

 Persistent memory bound metric under memory access analysis.

- Move write-sensitive data to DRAM
- Increase Intel®
 Optane™ DC
 persistent memory
 modules. 6 modules
 per socket is ideal.
 This will give you
 more bandwidth.



APPDIRECT MODE

OPTIMIZATION OPPORTUNITY: ACCESS PATTERN

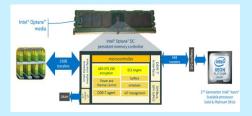


Workload Behavior:

Random media access pattern

Why?

Will not take advantage of 256B transfers



How to detect this opportunity?

Use Intel® VTune™ Platform Profiler

- Stream data in aligned 256B chunks
- Don't stream from multiple media locations in parallel

MEMORY MODE

OPTIMIZATION OPPORTUNITY: CACHE LOCALITY

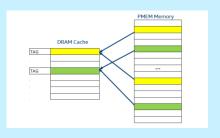


Workload Behavior:

Sensitivity to DRAM cache misses

Why?

Working set size > DRAM capacity results in conflict misses



How to detect this opportunity?

Use Intel® VTune™ Platform Profiler Memory Mode analysis

 Near memory cache read miss rate % metric

Use Intel® VTune™ Amplifier XE: Memory Access

 DRAM cache hit ratio under memory-access analysis.

- Improve DRAM Cache locality
- Consider using AppDirect volatile memory
- Ideal DRAM memory capacity: Intel® Optane DC persistent memory ratio = 1:4 or 1:8



APPDIRECT MODE & MEMORY MODE

OPTIMIZATION OPPORTUNITY: DIRECTORY OVERHEAD

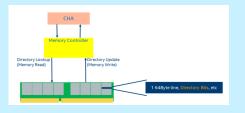


Workload Behavior:

Unnecessary Crosssocket accesses

Why?

Directory maintenance uses memory bandwidth



How to detect this opportunity?

Use Intel® VTune™ Platform Profiler

 Extra write bandwidth due to Directory Updates metric

- Optimize for NUMA
- Eliminate false sharing across sockets
- Investigate BIOS settings



APPDIRECT MODE & MEMORY MODE

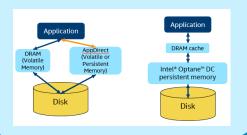
OPTIMIZATION OPPORTUNITY: DISK ACCESSES



Workload Behavior:Disk I/O

Why?

Accessing data in Intel® Optane DC persistent memory is preferred



How to detect this opportunity?

Use Intel® VTune™ Platform Profiler : I/O view

IOPS metric

Use Intel® VTune™ Amplifier XE : Input and Output analysis

Potential Optimizations:

 Keep working dataset in Intel® Optane DC persistent memory



SUMMARY

Architected for Persistence, Optimized for Performance

- Offers Persistent capabilities
- Near DRAM latency and faster than SSDs

Flexibility In Operation

- Choose between two modes
 - Memory mode for large affordable volatile memory
 - App Direct mode for persistent memory

Monitor and Tune!

- Take advantage of the modes effectively
- Various software tools available to monitor



RESOURCES: DOWNLOAD THE TOOLS, GET THE TRAINING

Intel® VTune™ Amplifier – Performance Profiler

software.intel.com/vtune

Intel® Inspector –
Persistence and Thread Debugger

software.intel.com/inspector

Intel® Optane™ DC Persistent Memory Technical Articles:

- software.intel.com/persistentmemory/tools
- software.intel.com/articles/prepare-forthe-next-generation-of-memory

SPDK / DPDK Technical Articles:

- User guide: SPDK IO Data View software.intel.com/vtune-amplifier-help-spdk-codeanalysis
- IO Issues: Remote socket access software.intel.com/vtune-amplifier-cookbook-i/o-issues-remote-socket-accesses



BACKUP

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CONFIGURATION FOR "P4800 AND P4610

SSDs

Intel-tested: Measured using FIO 3.1. Common Configuration - Intel 2U Server System, OS CentOS 7.5, kernel 4.17.6-1.el7.x86_64, CPU 2 x Intel® Xeon® 6154 Gold @ 3.0GHz (18 cores), RAM 256GB DDR4 @ 2666MHz. Configuration − Intel® Optane™ SSD DC P4800X 375GB and Intel® SSD DC P4610 3.2TB. Intel Microcode: 0x2000043; System BIOS: 00.01.0013; ME Firmware: 04.00.04.294; BMC Firmware: 1.43.91f76955; FRUSDR: 1.43. The benchmark results may need to be revised as additional testing is conducted. Performance results are based on testing as of November 15, 2018 and may not reflect all publicly available security updates. See configuration disclosure for details. No product can be absolutely secure.



INTEL® OPTANE™ DC PERSISTENT MEMORY LOADED LATENCY CURVE CONFIG

Component	Single DIMM Config
Test by	Intel
Test date	02/20/2019
Platform	NeonCity
Chipset	LBG B1
CPU	CLX B0 28 Core (8276), 1S
DDR Speed	2666 MT/s
AEP	QS Tranche3, 256GB, 18W
Memory Config	1 channel 32GB DDR4 (per socket) 256GB AEP (per socket)
AEP FW	5336
BIOS	573.D10
BKC version	WW08 BKC
Linux OS	4.20.4-200.fc29
Spectre/ Meltdown	Patched (1,2,3, 3a)
Performance Turning	QoS Disabled, IODC=5(AD)

All SKUs, frequencies, and performance estimates are **PRELIMINARY** and can change without notice.



